



#### SINGLE N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
	18mΩ @ V <sub>GS</sub> = 10V	9.0A
30V	30mΩ @ V <sub>GS</sub> = 4.5V	7.0A

### **Description and Applications**

This MOSFET has been designed to minimize the on-state resistance  $(R_{DS(on)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters
- •

### **Features and Benefits**

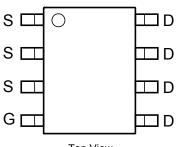
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

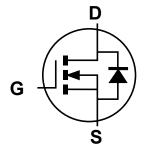
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper lead frame.
   Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.074 grams (approximate)







Top View Internal Schematic



Equivalent circuit

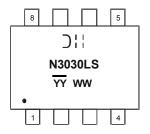
#### Ordering Information (Note 4)

Part Number	Case	Packaging		
DMN3030LSS-13	SO-8	2500/Tape & Reel		

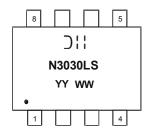
Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



Chengdu A/T Site



Shanghai A/T Site

);; = Manufacturer's Marking
N3030LS = Product Type Marking Code
YYWW = Date Code Marking
YY or YY = Year (ex: 13 = 2013)
WW = Week (01 - 53)

YY = Date Code Marking for SAT (Shanghai Assembly/ Test site)
YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)



## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±25	V
Drain Current (Note 5)	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	9.0 6.75	А
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	40	Α

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$P_{D}$	2.5	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ hetaJA}$	50	°C/W
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-55 to +150	°C

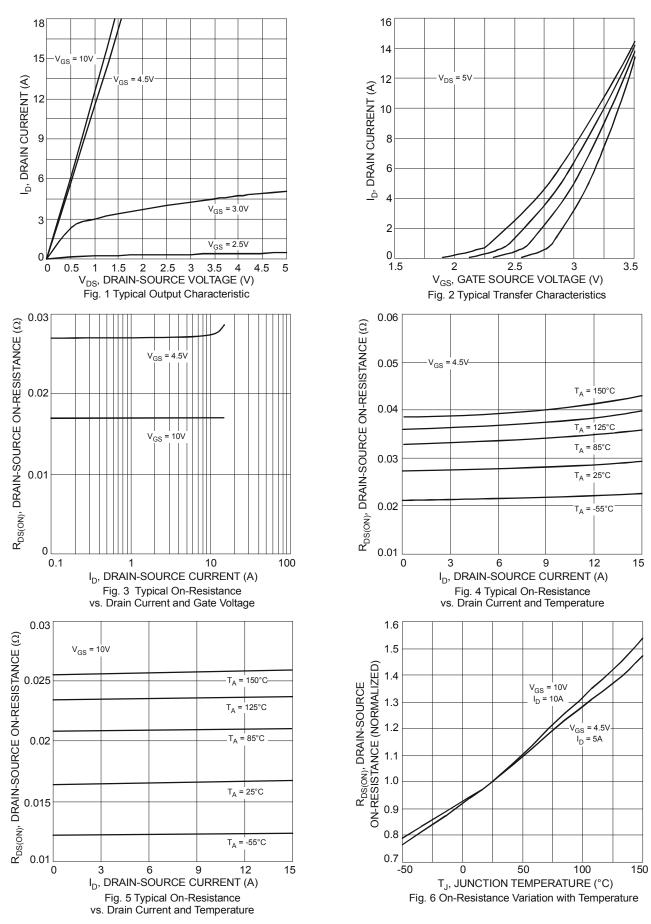
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	$BV_{DSS}$	30	_		V	$V_{GS} = 0V$ , $I_D = 250\mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μA	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)		_	_	±1	μA	$V_{GS} = \pm 25V$ , $V_{DS} = 0V$
, ,	.,		i	0.4		1,, ,, ,, ,, ,,
Gate Threshold Voltage	V <sub>GS(th)</sub>	1	_	2.1	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)		15.7	18	mΩ	$V_{GS} = 10V, I_D = 9A$
Static Brain-Source On-Resistance	INDS (ON)	_	26.4	30	11122	$V_{GS} = 4.5V, I_D = 7A$
Forward Transconductance	<b>g</b> fs	_	5.8		S	$V_{DS} = 10V, I_{D} = 9A$
Diode Forward Voltage	$V_{SD}$	0.5	0.7	1.2	V	$V_{GS} = 0V, I_S = 2.1A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C <sub>iss</sub>	_	741	_	pF	45)()(
Output Capacitance	Coss	_	124	_	pF	$V_{DS} = 15V, V_{GS} = 0V$ -f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	_	95	_	pF	
Gate Resistance	R <sub>G</sub>	0.30	0.88	2.5	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
SWITCHING CHARACTERISTICS (Note 8)						
Total Gate Charge	0	_	7.6	12	nC	$V_{DS} = 15V$ , $V_{GS} = 4.5V$ , $I_{D} = 9A$
Total Gate Charge	$Q_g$	_	16.7	25		V <sub>DS</sub> = 15V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 9A
Gate-Source Charge	$Q_{gs}$	_	1.9		IIC	
Gate-Drain Charge	$Q_{gd}$	_	5.2			
Turn-On Delay Time	t <sub>d(on)</sub>	_	4.0	_		
Rise Time	t <sub>r</sub>		4.4		20	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 15V,
Turn-Off Delay Time	t <sub>d(off)</sub>		23.0		ns	$R_L = 15\Omega$ , $R_G = 6\Omega$
Fall Time	t <sub>f</sub>		9.4			

Notes:

- 5. Device mounted on 2 oz copper pad layout with  $R_{0JA}$  = 50°C/W. 6. Pulse width ≤10µS, Duty Cycle ≤1%. 7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.







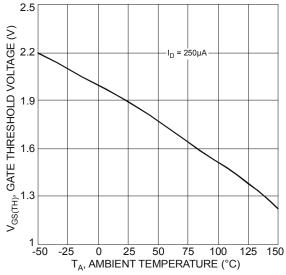
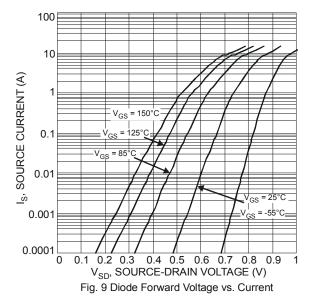
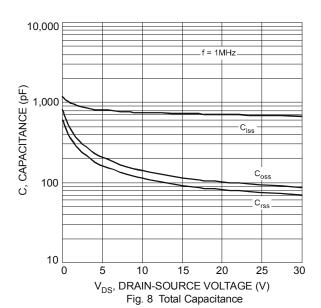


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





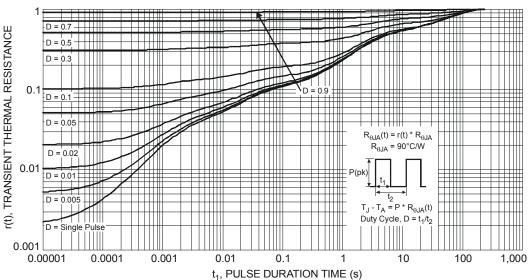
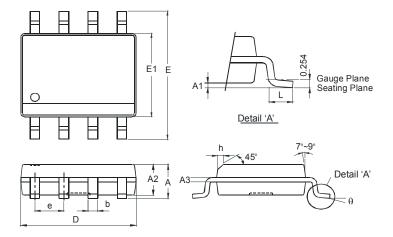


Fig. 10 Transient Thermal Response



## **Package Outline Dimensions**

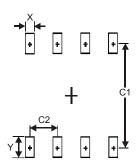
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SO-8					
Dim	Min	Max			
Α	-	1.75			
<b>A1</b>	0.10	0.20			
A2	1.30	1.50			
A3	0.15	0.25			
b	0.3	0.5			
D	4.85	4.95			
Е	5.90	6.10			
E1	3.85	3.95			
е	1.27 Typ				
h	-	0.35			
L	0.62	0.82			
θ	0°	8°			
All Dimensions in mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
Х	0.60		
Υ	1.55		
C1	5.4		
C2	1.27		



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